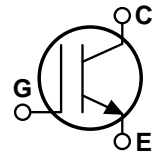
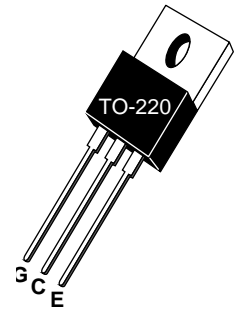


Thunderbolt IGBT™

The Thunderbolt IGBT™ is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Thunderbolt IGBT™ offers superior ruggedness and ultrafast switching speed.

- Low Forward Voltage Drop
- Low Tail Current
- Avalanche Rated
- High Freq. Switching to 150KHz
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT8GT60KR	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{GE}	Gate-Emitter Voltage	± 20	
V_{GEM}	Gate-Emitter Voltage Transient	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	16	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	8	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	34	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	34A @ 600V	
P_D	Total Power Dissipation	69	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 1.0mA$)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1mA, T_J = 25^\circ\text{C}$)	3	4	5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 8A, T_J = 25^\circ\text{C}$)		2.0	2.5	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 8A, T_J = 125^\circ\text{C}$)			2.8	
I_{CES}	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			20	μA
	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			700	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS
APT8GT60KR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		365		pF	
C_{oes}	Output Capacitance			43			
C_{res}	Reverse Transfer Capacitance			22			
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 8A$		7.5		V	
Q_g	Total Gate Charge ^③			34		nC	
Q_{ge}	Gate-Emitter Charge			5			
Q_{gc}	Gate-Collector ("Miller") Charge			15			
SSOA	Switching SOA	$T_J = 150^\circ\text{C}, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	34			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 8A$ $R_G = 5\Omega$ $T_J = +25^\circ\text{C}$		8		ns	
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-off Delay Time			30			
t_f	Current Fall Time			58			
E_{on1}	Turn-on Switching Energy ^④				TBD		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				75		
E_{off}	Turn-off Switching Energy ^⑥				82		
$t_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 8A$ $R_G = 5\Omega$ $T_J = +125^\circ\text{C}$		8		ns
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-off Delay Time			47			
t_f	Current Fall Time			53			
E_{on1}	Turn-on Switching Energy ^④				TBD		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				168		
E_{off}	Turn-off Switching Energy ^⑥				122		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			1.80	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			N/A	
W_T	Package Weight			1.9	gm

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② For Combi devices, I_{ces} includes both IGBT and FRED leakages
- ③ See MIL-STD-750 Method 3471.
- ④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)
- ⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. A Combi device is used for the clamping diode as shown in the E_{on2} test circuit. (See Figures 21, 22.)
- ⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT8GT60KR

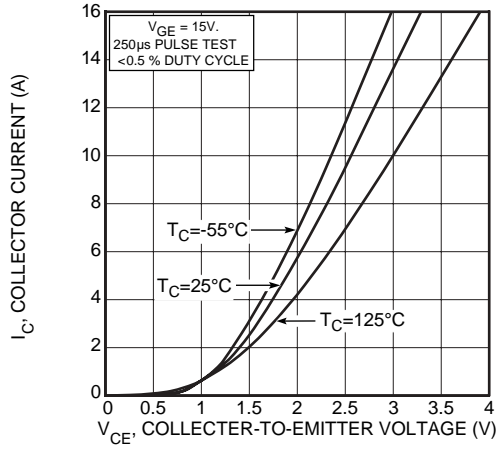


FIGURE 1, Output Characteristics ($V_{GE} = 15V$)

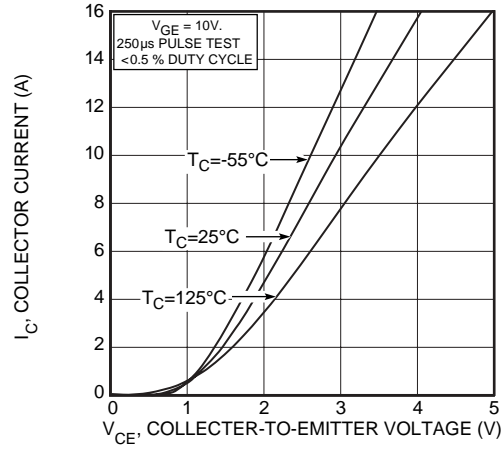


FIGURE 2, Output Characteristics ($V_{GE} = 10V$)

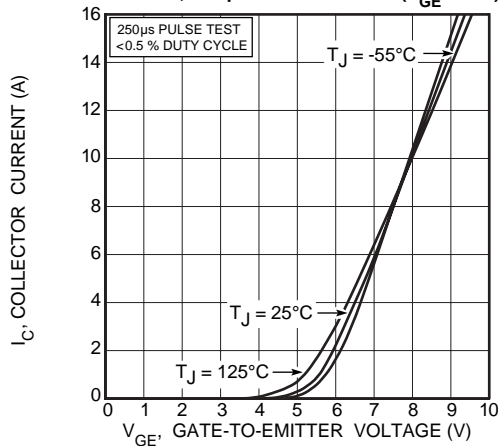


FIGURE 3, Transfer Characteristics

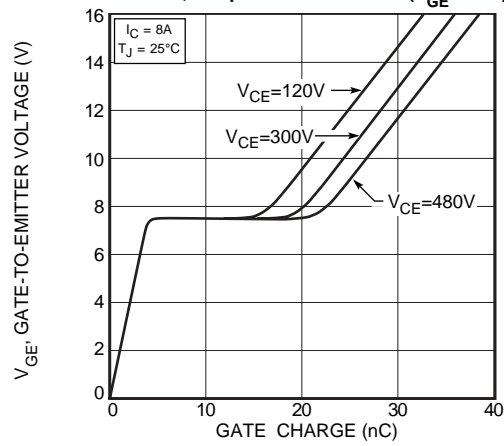


FIGURE 4, Gate Charge

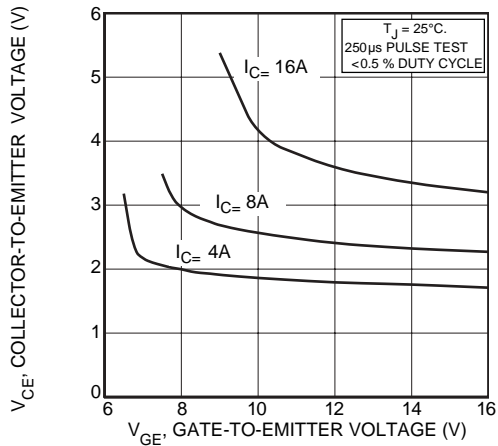


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

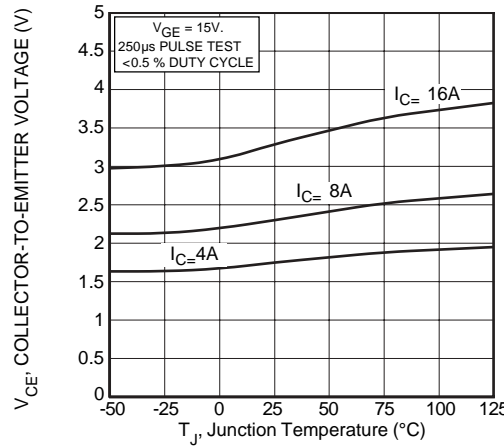


FIGURE 6, On State Voltage vs Junction Temperature

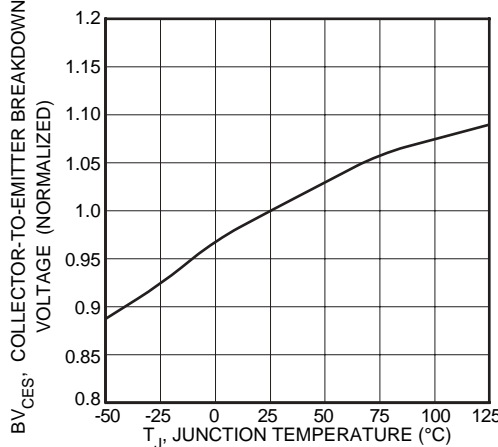


FIGURE 7, Breakdown Voltage vs. Junction Temperature

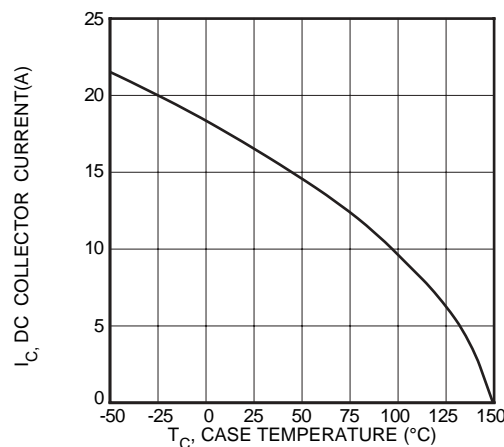


FIGURE 8, DC Collector Current vs Case Temperature

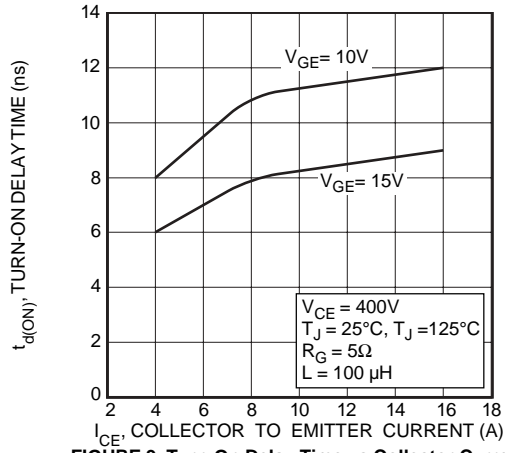


FIGURE 9, Turn-On Delay Time vs Collector Current

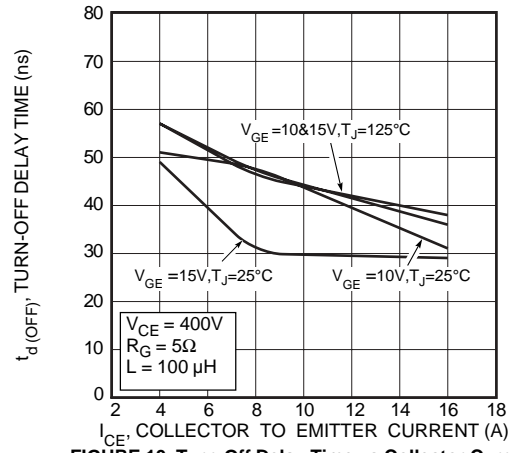


FIGURE 10, Turn-Off Delay Time vs Collector Current

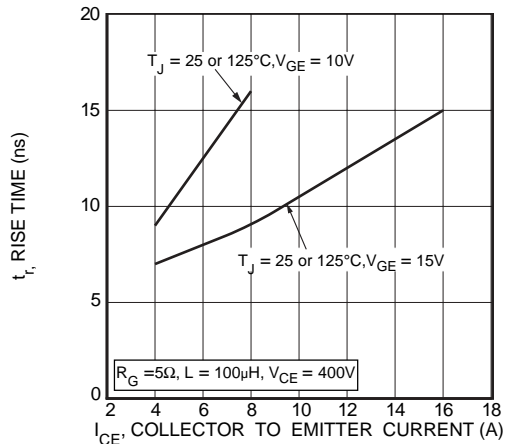


FIGURE 11, Current Rise Time vs Collector Current

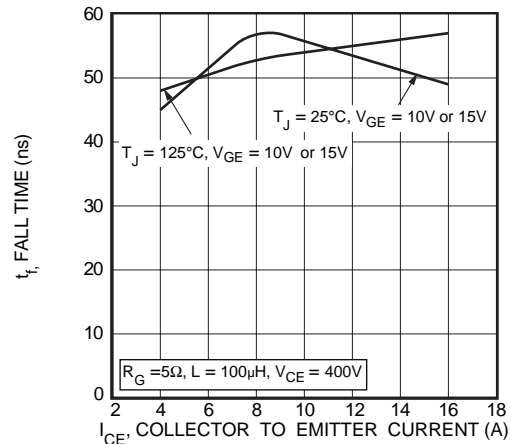


FIGURE 12, Current Fall Time vs Collector Current

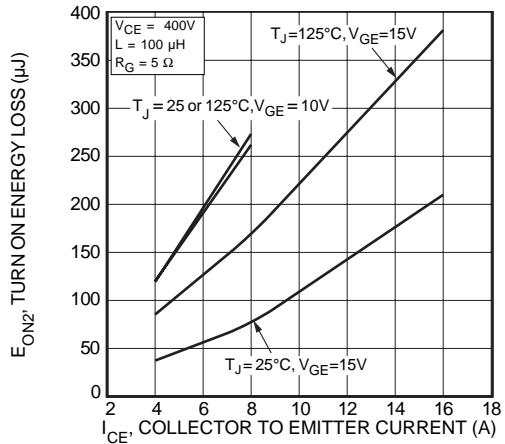


FIGURE 13, Turn-On Energy Loss vs Collector Current

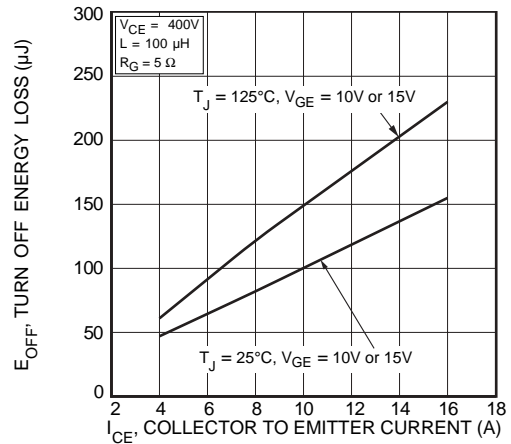


FIGURE 14, Turn Off Energy Loss vs Collector Current

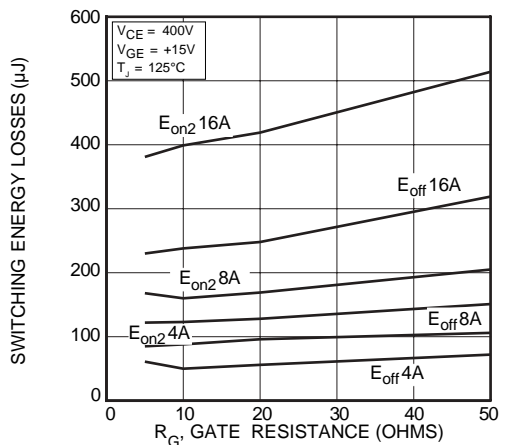


FIGURE 15, Switching Energy Losses vs. Gate Resistance

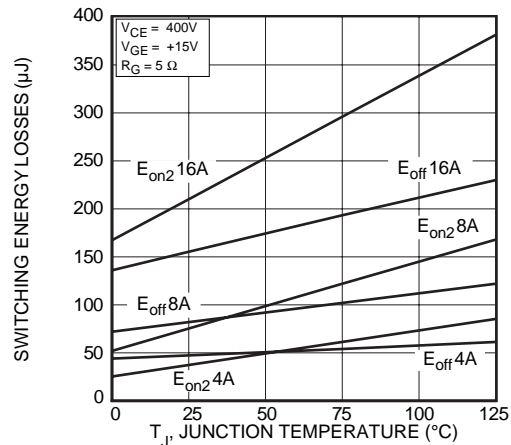


FIGURE 16, Switching Energy Losses vs Junction Temperature

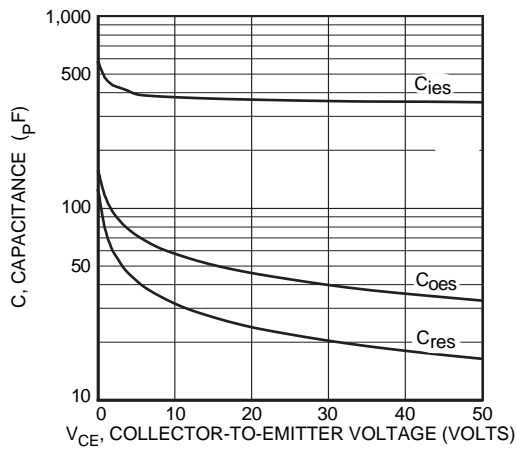


Figure 17, Capacitance vs Collector-To-Emitter Voltage

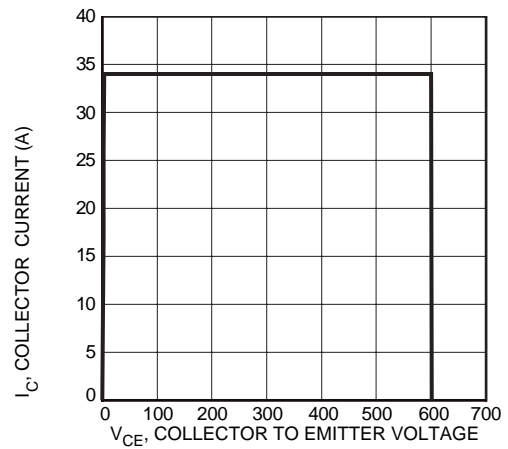


Figure 18, Minimum Switching Safe Operating Area

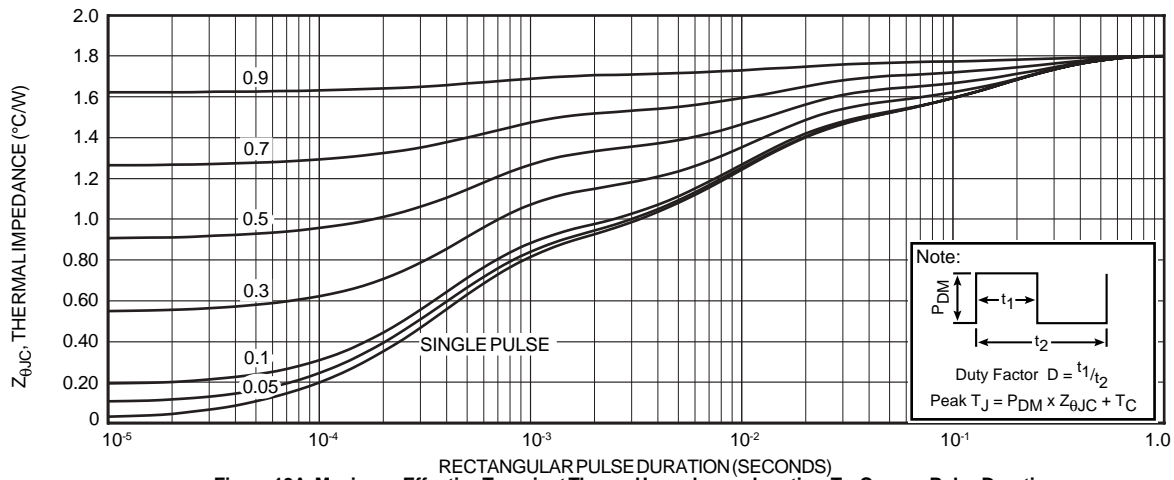


Figure 19A, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

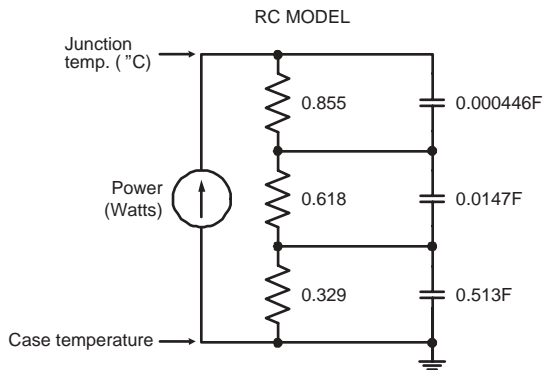


FIGURE 19B, TRANSIENT THERMAL IMPEDANCE MODEL

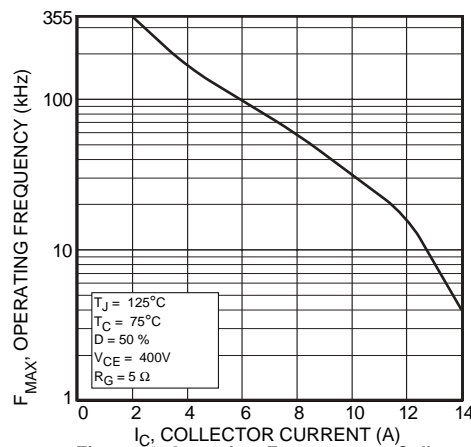


Figure 20, Operating Frequency vs Collector Current

$$F_{max} = \min(f_{max1}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$

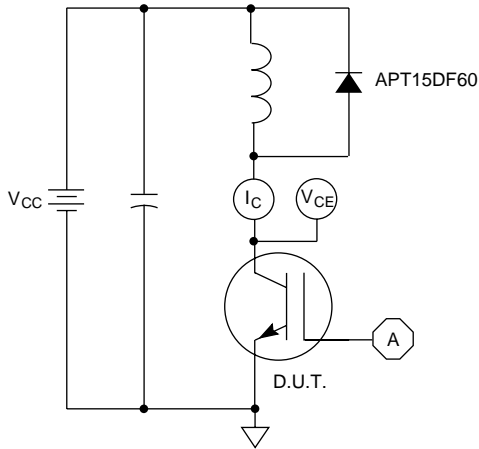


Figure 21, Inductive Switching Test Circuit

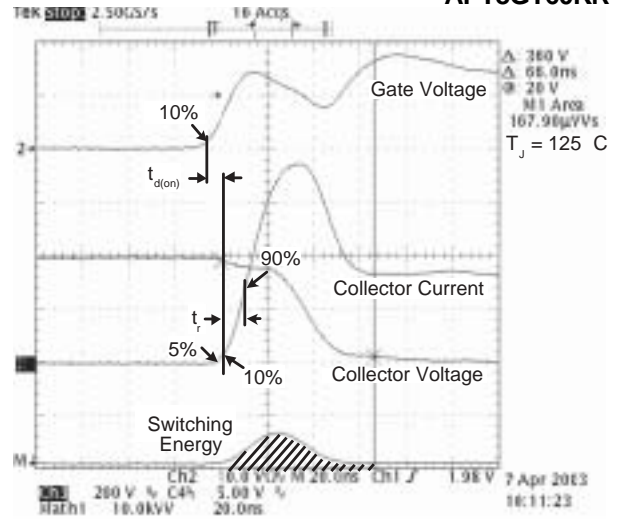


Figure 22, Turn-on Switching Waveforms and Definitions

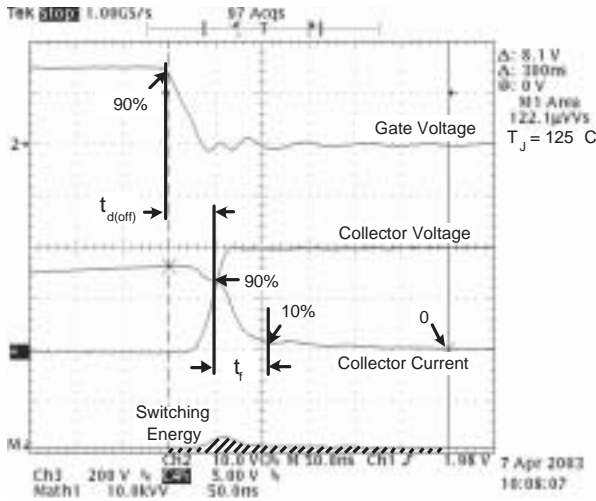


Figure 23, Turn-off Switching Waveforms and Definitions

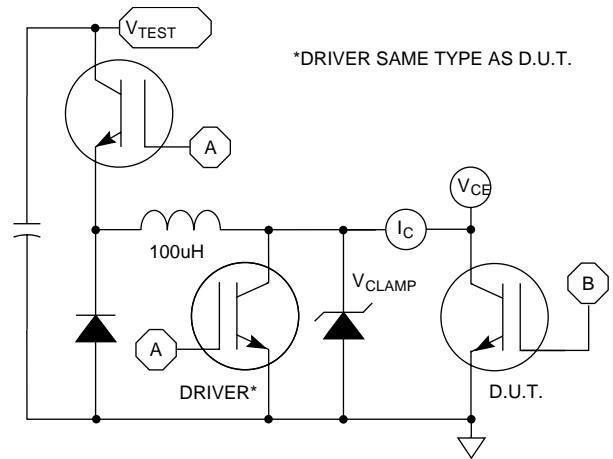
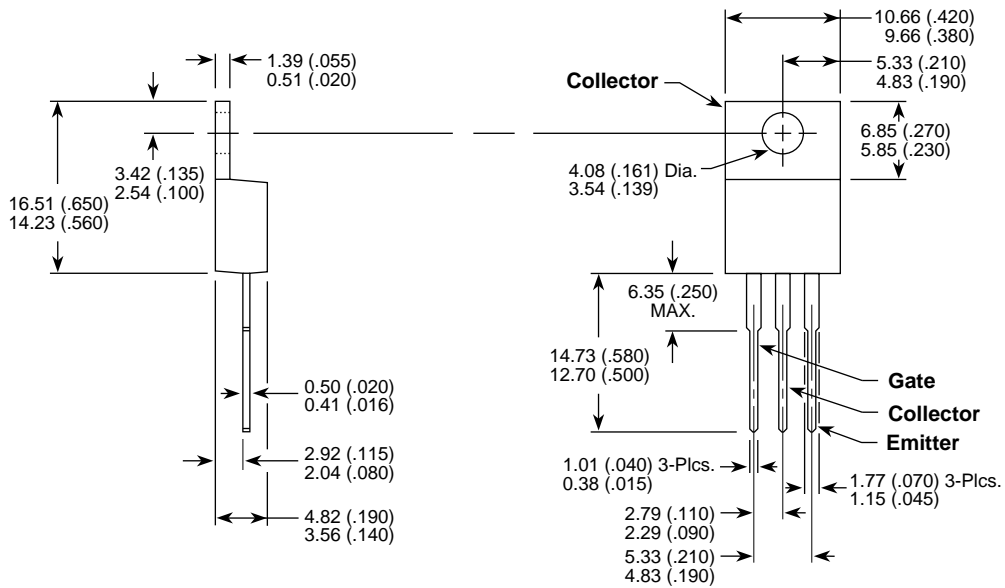


Figure 24, E_{ON1} Test Circuit

TO-220AC Package Outline



Dimensions in Millimeters and (Inches)